# PDTC144V series

NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 10 k $\Omega$ Rev. 04 — 16 November 2009 Product data sl

Product data sheet

### **Product profile**

### 1.1 General description

NPN resistor-equipped transistors.

Table 1. **Product overview** 

Type number	Package	Package	
	NXP	JEITA	
PDTC144VE	SOT416	SC-75	PDTA144VE
PDTC144VK	SOT346	SC-59A	PDTA144VK
PDTC144VM	SOT883	SC-101	PDTA144VM
PDTC144VS[1]	SOT54 (TO-92)	SC-43A	PDTA144VS
PDTC144VT	SOT23	-	PDTA144VT
PDTC144VU	SOT323	SC-70	PDTA144VU

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2).

#### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

### 1.3 Applications

- General-purpose switching and amplification
- Inverter and interface circuits

Circuit drivers

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.17	0.21	0.26	



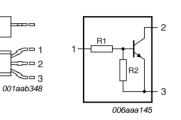
## 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
PIII	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		1 2
3	GND (emitter)	001aab347	R1 R2

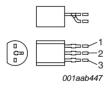
-	~ =	-	
-50	.) I	54	LΑ

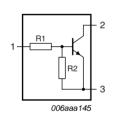
1	input (base)
2	output (collector)
3	GND (emitter)



#### **SOT54** variant

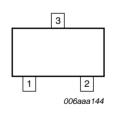
1	input (base)
2	output (collector)
3	GND (emitter)

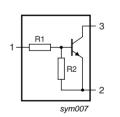




### SOT23, SOT323, SOT346, SOT416

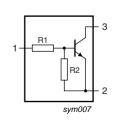
1	input (base)
2	GND (emitter)
3	output (collector)





#### **SOT883**

1	input (base)
2	GND (emitter)
3	output (collector)



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NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 10 k $\Omega$ 

#### **Ordering information** 3.

**Ordering information** Table 4.

Type number	Package	ge				
	Name	Description	Version			
PDTC144VE	SC-75	plastic surface mounted package; 3 leads	SOT416			
PDTC144VK	SC-59A	plastic surface mounted package; 3 leads	SOT346			
PDTC144VM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.5 mm	SOT883			
PDTC144VS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			
PDTC144VT	-	plastic surface mounted package; 3 leads	SOT23			
PDTC144VU	SC-70	plastic surface mounted package; 3 leads	SOT323			

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

### **Marking**

**Product data sheet** 

Table 5. Marking codes

Table of Market Specific	
Type number	Marking code <sup>[1]</sup>
PDTC144VE	18
PDTC144VK	29
PDTC144VM	G6
PDTC144VS	TC144V
PDTC144VT	*AA
PDTC144VU	*18

<sup>[1] \* = -:</sup> made in Hong Kong

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

### 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	-	15	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-15	V
Io	output current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation				
	SOT416	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> -	150	mW
	SOT346	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> -	250	mW
	SOT883	$T_{amb} \le 25  ^{\circ}C$	[2][3]	250	mW
	SOT54	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> -	500	mW
	SOT23	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> -	250	mW
	SOT323	$T_{amb} \le 25  ^{\circ}C$	[1] -	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

<sup>[1]</sup> Refer to standard mounting conditions.

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> _	-	833	K/W
	SOT346		<u>[1]</u> _	-	500	K/W
	SOT883		[2][3]	-	500	K/W
	SOT54		<u>[1]</u> _	-	250	K/W
	SOT23		<u>[1]</u> _	-	500	K/W
	SOT323		<u>[1]</u> _	-	625	K/W

<sup>[1]</sup> Refer to standard mounting conditions.

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<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

<sup>[3]</sup> Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 µm copper strip line.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

<sup>[3]</sup> Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 μm copper strip line.

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NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 10 k $\Omega$ 

### **Characteristics**

Table 8. Characteristics

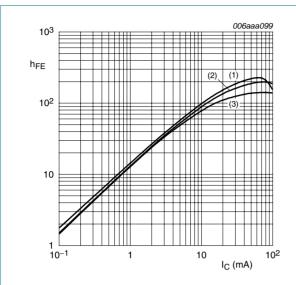
**Product data sheet** 

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	150	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	40	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	3.1	1	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 300 \text{ mV}; I_{C} = 2 \text{ mA}$	6	3.8	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.17	0.21	0.26	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2	pF

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NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 10 k $\Omega$ 



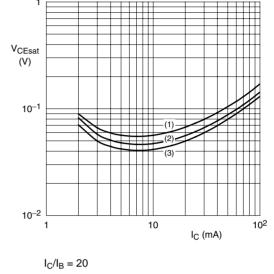
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values

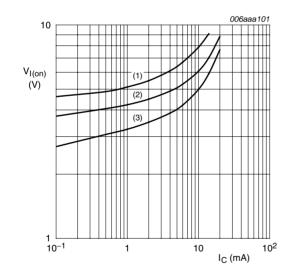


(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



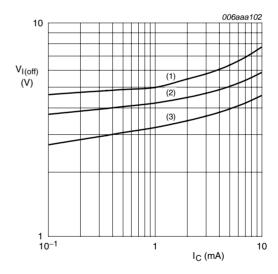
$$V_{CE} = 0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

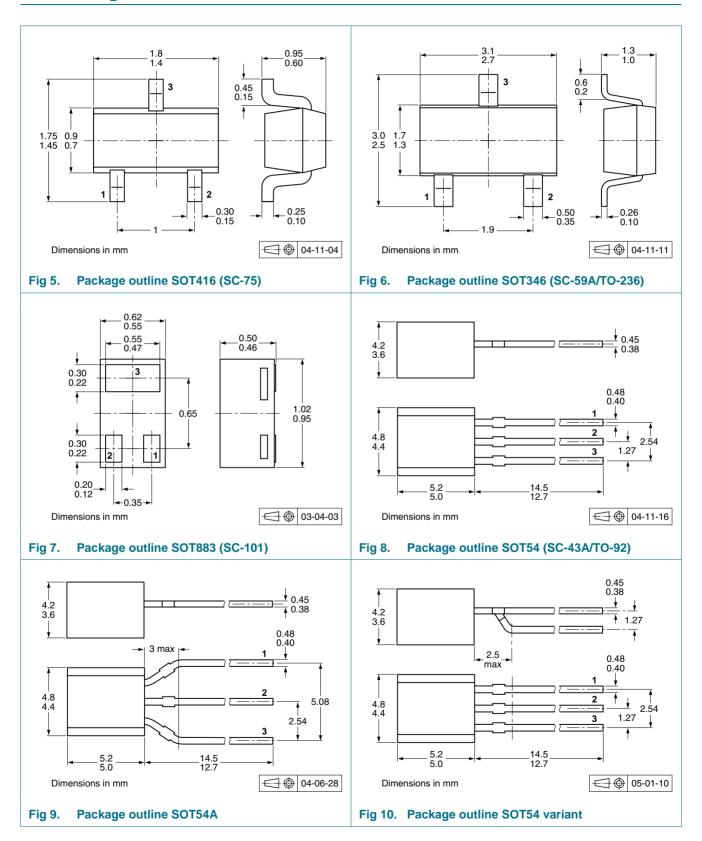
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

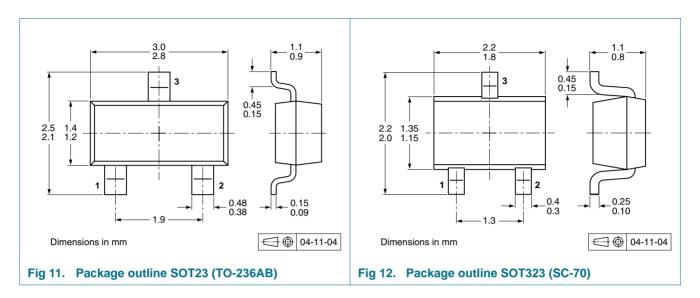
(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. Off-state input voltage as a function of collector current; typical values

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### 8. Package outline





## 9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PDTC144VE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC144VK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC144VM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
PDTC144VS	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PDTC144VT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
PDTC144VU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135

<sup>[1]</sup> For further information and the availability of packing methods, see Section 12.



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NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 10 k $\Omega$ 

## 10. Revision history

### Table 10. Revision history

**Product data sheet** 

Document ID	Release date	Data sheet status	Change notice	tice Supersedes	
PDTC144V_SER_4	20091116	Product data sheet	-	PDTC144V_SER_3	
Modifications:		eet was changed to reflect w legal definitions and discl			
PDTC144V_SER_3	20050215	Product data sheet	-	PDTC144VT_2	
PDTC144VT_2	20040511	Objective data sheet	-	PDTC144VT_1	
PDTC144VT_1	20040305	Objective data sheet	-	-	

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#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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## **PDTC144V** series

### NPN resistor-equipped transistors; $R1 = 47 \text{ k}\Omega$ , $R2 = 10 \text{ k}\Omega$

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